# **MMBT3904**

Rev.E Mar.-2016



# 描述 / Descriptions

SOT-23 塑封封装 NPN 半导体三极管。Silicon NPN transistor in a SOT-23 Plastic Package.

### 特征 / Features

低电压,低电流。

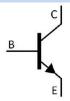
Low current, Low voltage.

# 用途 / Applications

用于普通放大及开关。

General purpose amplifier and switching.

# 内部等效电路 / Equivalent Circuit



# 引脚排列 / Pinning



PIN 1 : Base PIN 2 : Emitter PIN 3 : Collector

# 放大及印章代码 / h<sub>FE</sub> Classifications & Marking

h <sub>FE</sub> Range	100~300		
Marking	H1A		

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# 极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数	符 <del>号</del>	数值	单位
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	60	V
Collector to Emitter Voltage	$V_{CEO}$	40	V
Emitter to Base Voltage	$V_{EBO}$	6.0	V
Collector Current	I <sub>C</sub>	200	mA
Collector Dower Dissination	Pc	200	mW
Collector Power Dissipation	*P <sub>C</sub>	350	mW
Junction Temperature	T <sub>j</sub>	150	${\mathbb C}$
Storage Temperature Range	T <sub>stg</sub>	-55∼150	${\mathbb C}$

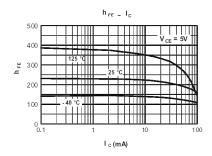
<sup>\*</sup>在 7×5×0.6mm 陶瓷板上 \*When mounted on a 7×5×0.6mm ceramic board

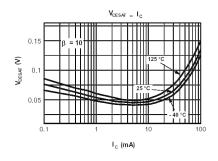
# 电性能参数 / Electrical Characteristics(Ta=25°C)

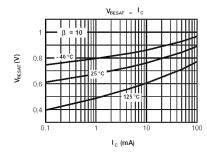
参数	符号	测试条件		最小值	典型值	最大值	单位
Parameter	Symbol	Test Conditions		Min	Тур	Max	Unit
Collector to Base Breakdown Voltage	$V_{CBO}$	I <sub>C</sub> =10μA	I <sub>E</sub> =0	60			V
Collector to Emitter Breakdown Voltage	$V_{CEO}$	I <sub>C</sub> =1.0mA	I <sub>B</sub> =0	40			V
Emitter to Base Breakdown Voltage	$V_{EBO}$	I <sub>E</sub> =10μA	I <sub>C</sub> =0	6.0			V
Collector Cut-Off Current	I <sub>CBO</sub>	V <sub>CB</sub> =30V	I <sub>E</sub> =0			0.05	μΑ
Emitter Cut-Off Current	I <sub>EBO</sub>	V <sub>EB</sub> =3.0V	I <sub>C</sub> =0			0.05	μA
	h <sub>FE(1)</sub>	V <sub>CE</sub> =1.0V	I <sub>C</sub> =10mA	100		300	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =1.0V	I <sub>C</sub> =100mA	30			
DC Current Gain	h <sub>FE(3)</sub>	V <sub>CE</sub> =1.0V	I <sub>C</sub> =50mA	60			
	h <sub>FE(4)</sub>	V <sub>CE</sub> =1.0V	I <sub>C</sub> =1.0mA	70			
	h <sub>FE(5)</sub>	V <sub>CE</sub> =1.0V	I <sub>C</sub> =0.1mA	40			
Collector-Emitter Saturation	V <sub>CE(sat)(1)</sub>	I <sub>C</sub> =10mA	I <sub>B</sub> =1.0mA			0.2	V
Voltage	V <sub>CE(sat)(2)</sub>	I <sub>C</sub> =50mA	I <sub>B</sub> =5.0mA			0.3	V
Dana Emilitar Catamatian Valtaria	V <sub>BE(sat)(1)</sub>	I <sub>C</sub> =10mA	I <sub>B</sub> =1.0mA	0.65		0.85	V
Base-Emitter Saturation Voltage	V <sub>BE(sat) (2)</sub>	I <sub>C</sub> =50mA	I <sub>B</sub> =5.0mA			0.95	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =20V f=100MHz	I <sub>C</sub> =10mA	300			MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =5.0V	f=1.0MHz			4.0	pF
Storage Time	t <sub>stg</sub>	V <sub>CC</sub> =3.0V I <sub>B1</sub> =-I <sub>B2</sub> =1.0r	I <sub>C</sub> =10mA mA			200	ns
Fall Time	t <sub>f</sub>	V <sub>CC</sub> =3.0V I <sub>C</sub> =10mA I <sub>B1</sub> =-I <sub>B2</sub> =1.0mA				50	ns
Delay Time	t <sub>d</sub>	$V_{CC}$ =3.0V $I_{C}$ =10mA	V <sub>BE</sub> =0.5V I <sub>B1</sub> =1.0mA			35	ns
Rise Time	t <sub>r</sub>	V <sub>CC</sub> =3.0V I <sub>C</sub> =10mA	V <sub>BE</sub> =0.5V I <sub>B1</sub> =1.0mA			35	ns
Input Capacitance	C <sub>ib</sub>	V <sub>EB</sub> =0.5V	f=1.0MHz			8.0	pF

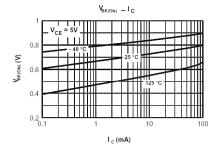


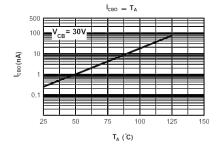
### 电参数曲线图 / Electrical Characteristic Curve

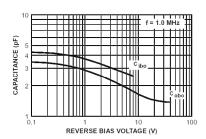


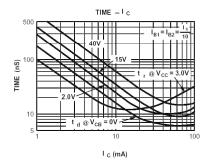


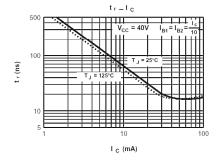


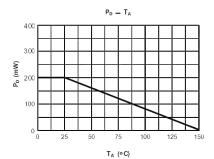












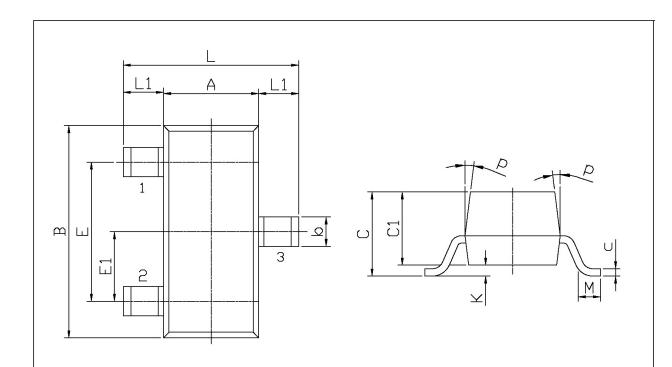
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# 外形尺寸图 / Package Dimensions

S0T-23

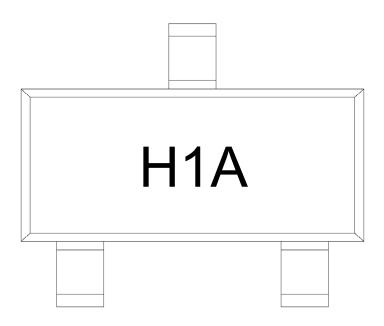
单位; mm



Symbol	Dimensions In Millmeters		S. and a st	Dimensions In Millmeters		
	Min	Max	Symbol	Min	Max	
L	2.2	2.7	С	1.30Ma×		
L1	0.45	0.65	C1	0.90	1.20	
Α	1,15	1.50	⊂ 0,05		0.20	
В	2,70	3.10	К	0	0.10	
E	1.70	2.10	М	0.20MIN		
E1	0.85	1.05	Р	7°		
b	0.35	0,55				



# 印章说明 / Marking Instructions



说明:

H:为公司代码1A:为型号代码

Note:

H: Company Code

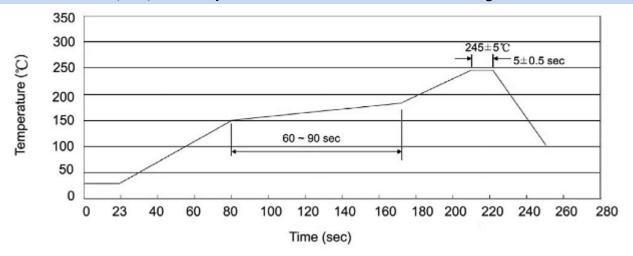
1A: Product Type Code

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### 回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明:

1、预热温度 25~150℃, 时间 60~90sec;

2、峰值温度 245±5℃, 时间持续为 5±0.5sec;

3、焊接制程冷却速度为 2~10℃/sec.

Note:

1.Preheating:25~150°C, Time:60~90sec.

2.Peak Temp.:245±5°C, Duration:5±0.5sec.

3. Cooling Speed: 2~10°C/sec.

#### 耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度:260±5℃ 时间:10±1 sec. Temp.:260±5℃ Time:10±1 sec

### 包装规格 / Packaging SPEC.

#### 卷盘包装 / REEL

Package Type Units 包装数量				Dimension 包装尺寸 (unit: mm³)				
封装形式	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7″ ×8	180×120×180	390×385×205

### 使用说明 / Notices